

**IN THE TITLE:**

Replace the title of the invention with the following title:

-- METHOD FOR ELIMINATING PROCESS BYPRODUCT DURING FABRICATION  
OF LIQUID CRYSTAL DISPLAY --.

**IN THE SPECIFICATION:**

Please amend paragraph [0039], as follows:

[0039] On the other hand, after the process byproduct elimination process is performed using the related art  $\text{SF}_6 + \text{O}_2$  gas, the photo resist pattern remaining on the ashed substrate 30 is more excessively ashed than the remaining photo resist pattern in the ashing process normally performed. In particular, the photo resist pattern formed at the positions six and eleven of the substrate 30 is excessively ashed, thereby leaving only about 3000 angstroms in thickness.

Further, if the ashing process is performed with an ashing gas ( $\text{SF}_6:\text{O}_2=1:20$ ) for 75 seconds after inserting the dummy substrate into the chamber, the photo resist pattern remaining on the ashed ~~dummy~~ substrate is more excessively ashed than the remaining photo resist pattern in the ashing process normally performed.